NTZD3154N

Small Signal MOSFET

20 V, 540 mA, Dual N−Channel

Features

- Low $R_{DS(on)}$ Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	20	V
Gate−to−Source Voltage			V_{GS}	±6.0	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	540	mA
		T_A = 85°C		390	
Power Dissipation (Note 1)	Steady State		P_D	250	mW
Continuous Drain Current (Note 1)	t ≤ 5 s	T_A = 25°C	I_D	570	mA
		T_A = 85°C		410	
Power Dissipation (Note 1)	t ≤ 5 s		P_D	280	mW
Pulsed Drain Current	t_p = 10 μs		I_{DM}	1.5	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	350	mA
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	500	°C/W
Junction−to−Ambient − t ≤ 5 s (Note 1)		447	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu. area = 1.127 in sq [1 oz] including traces).

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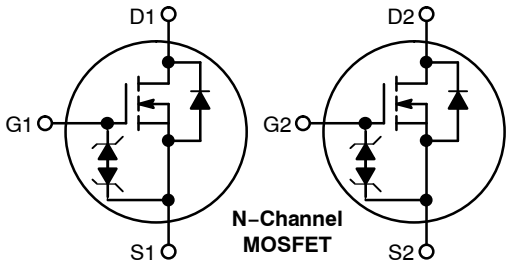
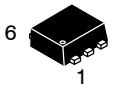
$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max (Note 1)
20	400 mΩ @ 4.5 V	540 mA
	500 mΩ @ 2.5 V	
	700 mΩ @ 1.8 V	





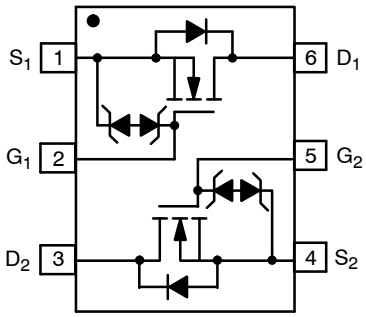
SOT−563−6
CASE 463A

MARKING DIAGRAM

TV = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

PINOUT: SOT−563



Top View

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted.)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		20	–	–	V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	–		–	14	–	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 16 V	T_J = 25°C	–	–	1.0	μA
			T_J = 125°C	–	–	5.0	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±4.5 V		–	–	±5.0	μA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		0.45	–	1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	–		–	2.0	–	mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 540 mA		–	0.4	0.55	Ω
		V_{GS} = 2.5 V, I_D = 500 mA		–	0.5	0.7	
		V_{GS} = 1.8 V, I_D = 350 mA		–	0.7	0.9	
Forward Transconductance	g_{FS}	V_{DS} = 10 V, I_D = 540 mA		–	1.0	–	S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 16 V		–	80	150	pF
Output Capacitance	C_{OSS}			–	13	25	
Reverse Transfer Capacitance	C_{RSS}			–	10	20	
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 10 V; I_D = 540 mA		–	1.5	2.5	nC
Threshold Gate Charge	$Q_{G(TH)}$			–	0.1	–	
Gate−to−Source Charge	Q_{GS}			–	0.2	–	
Gate−to−Drain Charge	Q_{GD}			–	0.35	–	
SWITCHING CHARACTERISTICS, V_{GS} = V (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DD} = 10 V, I_D = 540 mA, R_G = 10 Ω		–	6.0	–	ns
Rise Time	t_r			–	4.0	–	
Turn−Off Delay Time	$t_{d(OFF)}$			–	16	–	
Fall Time	t_f			–	8.0	–	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 350 mA	T_J = 25°C	–	0.7	1.2	V
			T_J = 125°C	–	0.6	–	
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, d_{ISD}/d_t = 100 A/μs, I_S = 350 mA		–	6.5	–	ns

2. Surface−mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).
3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤2%.
4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

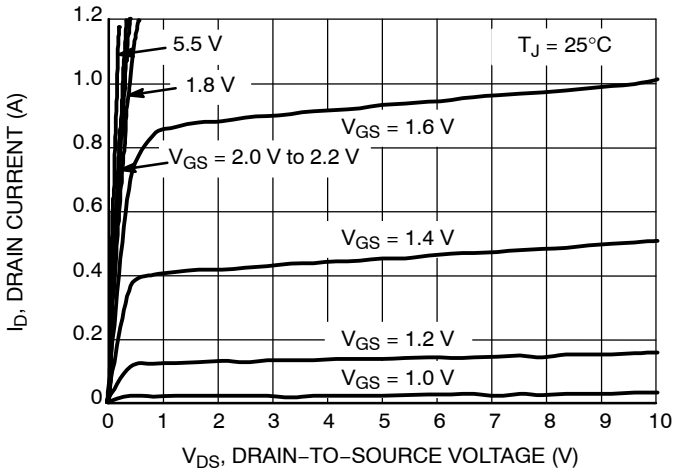


Figure 1. On−Region Characteristics

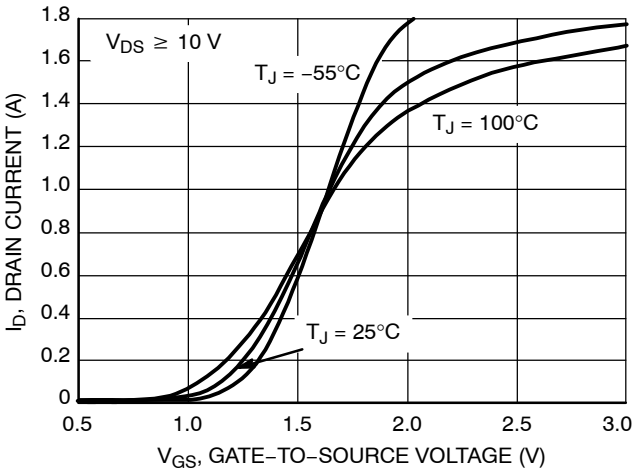


Figure 2. Transfer Characteristics

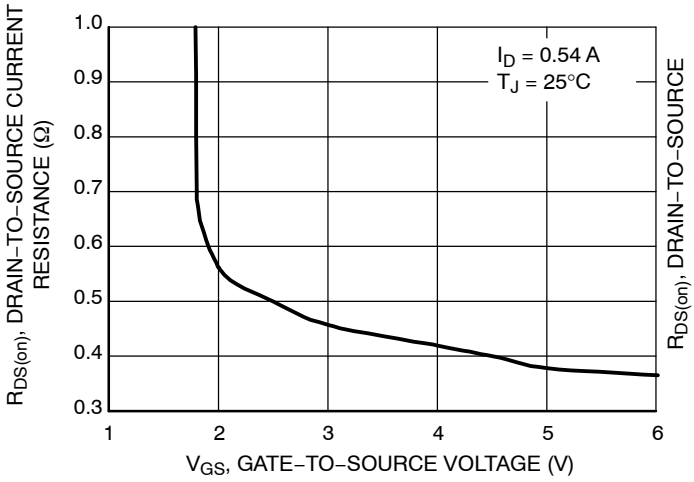


Figure 3. On−Resistance versus Gate−to−Source Voltage

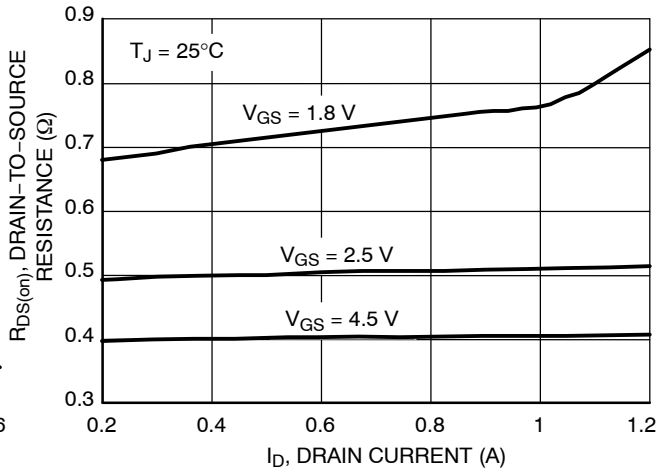


Figure 4. On−Resistance versus Drain Current and Gate Voltage

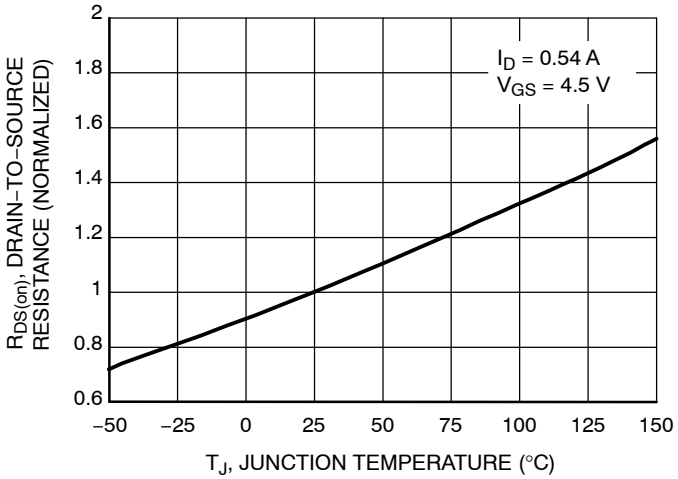


Figure 5. On−Resistance Variation with Temperature

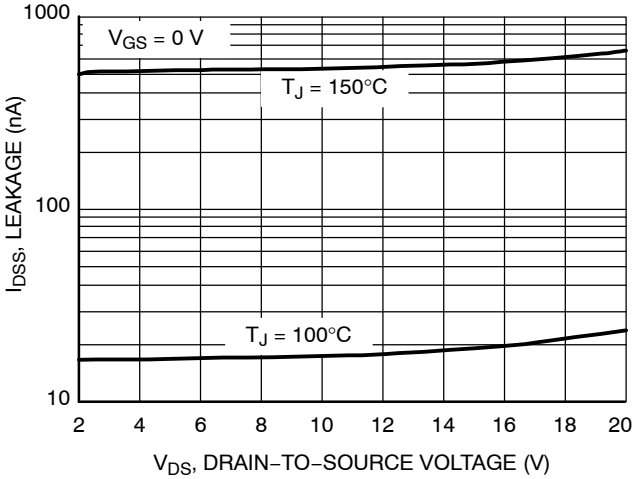


Figure 6. Drain−to−Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

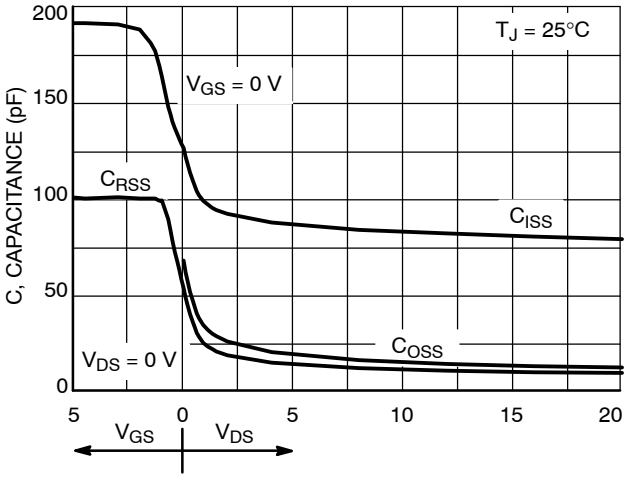


Figure 7. Capacitance Variation

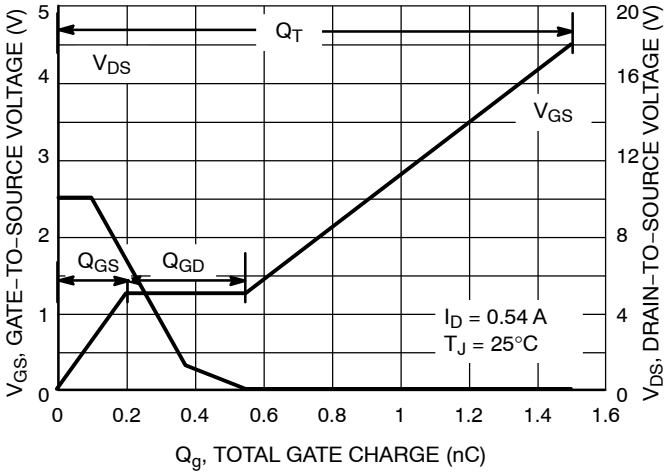


Figure 8. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

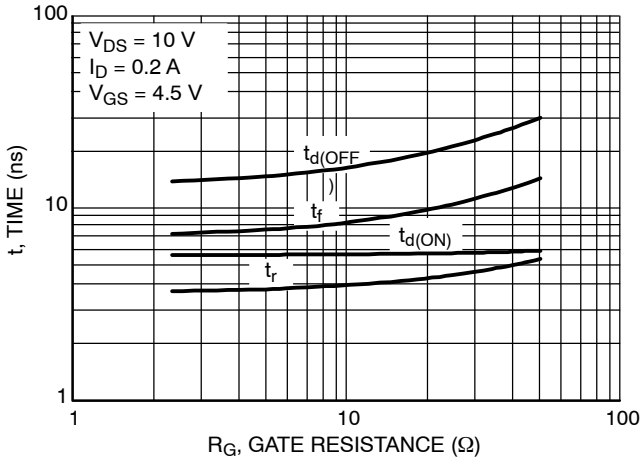


Figure 9. Resistive Switching Time Variation versus Gate Resistance

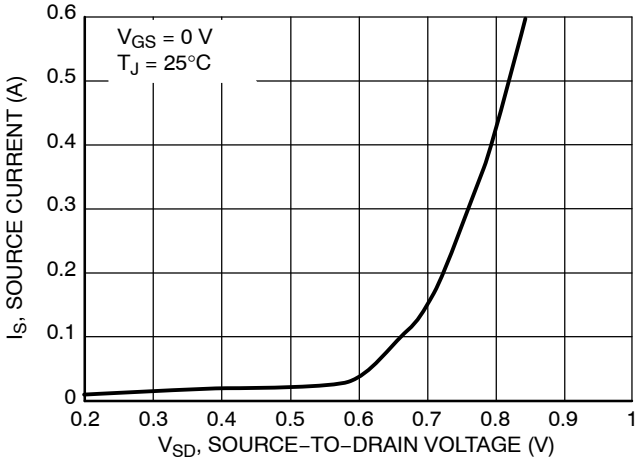


Figure 10. Diode Forward Voltage versus Current

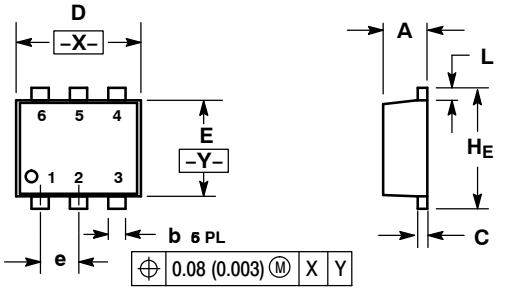
ORDERING INFORMATION

Device	Package	Shipping
NTZD3154NT1G	SOT−563 (Pb−Free)	4000 / Tape & Reel
NTZD3154NT1H		
NTZD3154NT2G		
NTZD3154NT2H		
NTZD3154NT5G		8000 / Tape & Reel
NTZD3154NT5H		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

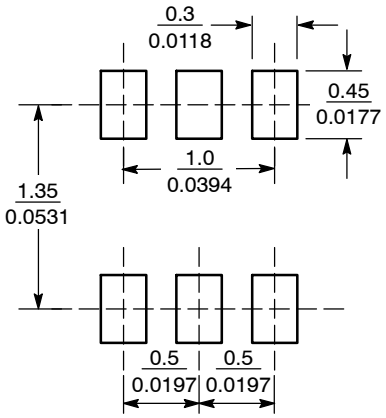
SOT−563, 6 LEAD
CASE 463A
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.062	0.066

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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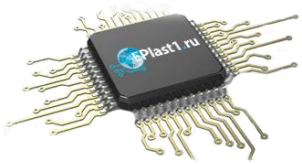
- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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